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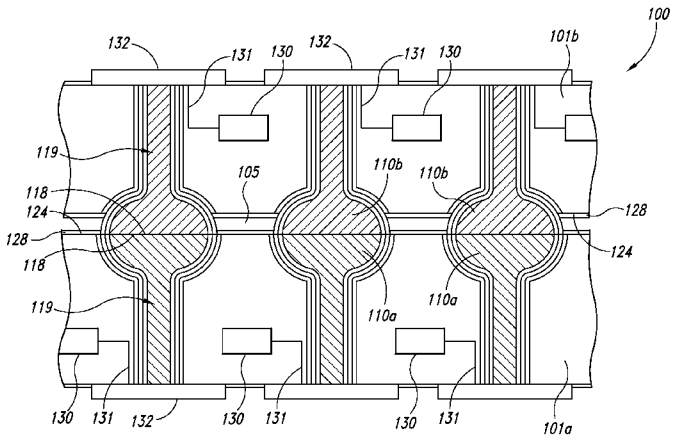


Fig. 2J

(57) Abstract: Semiconductor substrates with unitary vias and via terminals, and associated systems and methods are disclosed. A representative method in accordance with a particular embodiment includes forming a blind via (140) in a semiconductor substrate, applying a protective layer (122) to a sidewall surface of the via, and forming a terminal opening (111) by selectively removing substrate material from an end surface of the via, while protecting from removal substrate material against which the protective coating is applied. The method can further include disposing a conductive material in both the via and the terminal opening to form an electrically conductive terminal that is unitary with conductive material in the via. Substrate material adjacent to the terminal can then be removed to expose the terminal, which can then be connected to a conductive structure external to the substrate.

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